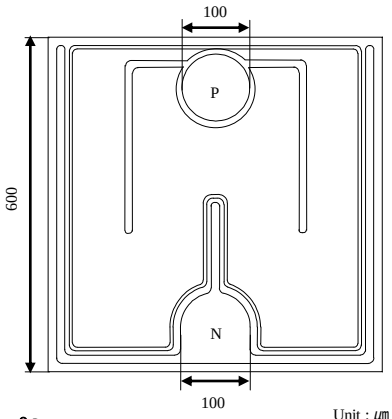
ULTRA VIOLET LED Chip

NS365C-3SAA
NS375C-3SAA

(1) Chip Description

●Mechanical Specification

Description	Dimension
Emission Area	512μm x 535μm
Bottom Area	600μm x600μm ± 20μm
Chip Thickness	120μm ± 20μm
N Bonding Pad Electrode	125μm ±5μm
P Bonding Pad Electrode	125μm ±5μm



Unit : μm

● Material

Substrate : Sapphire

Epitaxial Layer : GaN Based Material

N Bonding Pad Electrode : Au alloy

P Bonding Pad Electrode : Au alloy

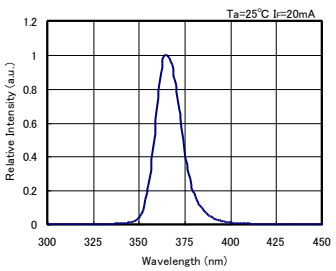
(2) Optical and Electrical Characteristics (Ta=25℃)

Item		Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	NS365C-3SAA	V_F	I_F=100mA	3.2	3.6	4.2	V
	NS375C-3SAA			3.2	3.6	4.2	
Reverse Current		I_R	V_R=5V	-	-	10	μA
Peak Wavelength*1	NS365C-3SAA	λ_p	I_F=100mA	363	-	370	nm
	NS375C-3SAA			375	-	380	
Full Width at Half Maximum		Δλ	I_F=100mA	10	-	20	nm
Optical Output Power *2		Po	I_F=100mA	Refer to Rank Information			mW

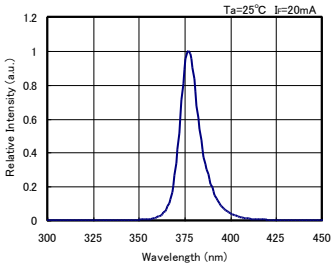
*1 Measurement error is ±2nm *2 Measurement error is ±10%

(3) Spectrum

NS365C-3SAA



NS375C-3SAA



■ Rank Information

Rank	Optical Output Power			NS365C-3SAA	NS375C-3SAA
	Min.	Typ.	Max.		
A1	5.0	-	10.0		
A2	10.0	-	15.0	○	
A3	15.0	-	20.0	○	
A4	20.0	-	25.0		
A5	25.0	-	30.0		○
A6	30.0	-	35.0		○

*3 Please contact us for availability.

CAUTION

・LEDs emit very strong UV radiation.
・Don't look directly into the LED light. UV radiation can harm your eyes.
・To prevent even inadequate exposure, wear protective eyewear.
・If LEDs are embedded in devices, please indicate warning labels against the UV light LED used.
・Keep out of reach of children.
・UV LED chips are very sensitive to static and surge. Take a full protection from static.

Specification and dimension are subject to change for improvement without notice.

NITRIDE SEMICONDUCTORS Co.,Ltd.

NITRIDE SEMICONDUCTORS Co., Ltd.
115-7 Itayashima, Akinokami, Seto-cho,
Naruto-shi, Tokushima 771-0360 JAPAN
TEL:+81-88-683-7750 FAX:+81-88-683-7751
URL: http://www.nitride.co.jp **Mail:** nitride@nitride.co.jp